

# NPN SILICON HIGH FREQUENCY TRANSISTOR

## DESCRIPTION:

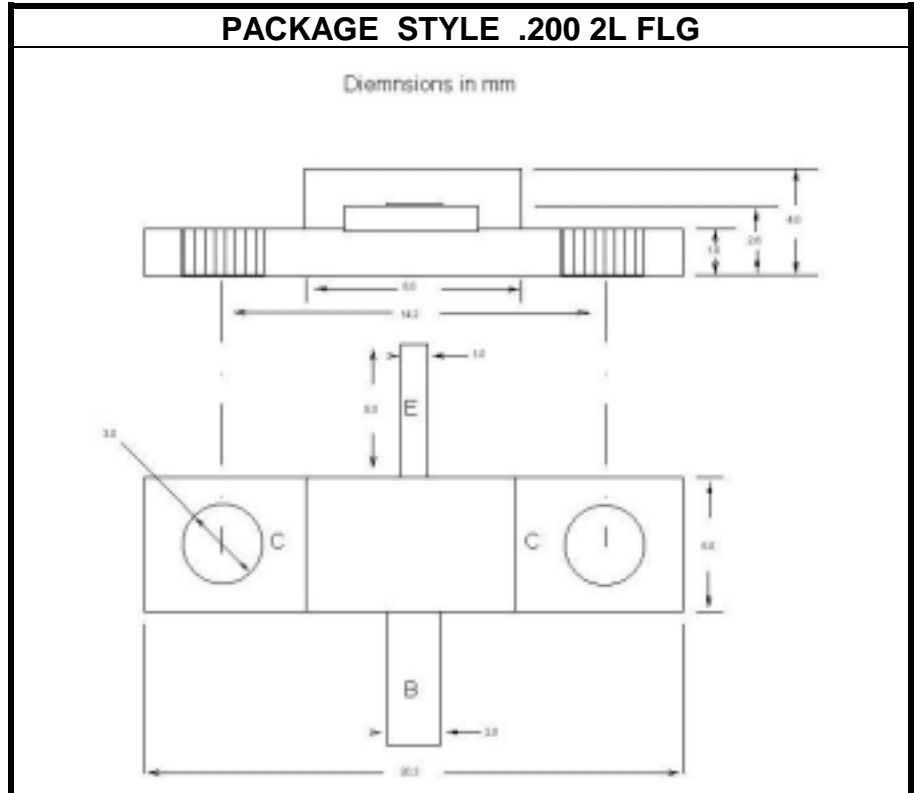
The **ASI 2SC2951** is a High Frequency Transistor Designed for General Purpose Oscillator Applications up to 10 GHz.

## FEATURES:

- $P_{osc} = 630 \text{ mW}$  Typical at 7.5 GHz
- **Omnigold™** Metallization System

## MAXIMUM RATINGS

$I_C$	440 mA
$V_{CE}$	16 V
$V_{CB}$	25 V
$P_{DISS}$	9.7 W @ $T_C = 25^\circ\text{C}$
$T_J$	-65 to +200 °C
$T_{STG}$	-65 to +200 °C
$\theta_{JC}$	18 °C/W



## CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$BV_{CEO}$	$I_C = 1.0 \text{ mA}$			16			V
$BV_{CBO}$	$I_C = 100 \mu\text{A}$			25			V
$BV_{EBO}$	$I_E = 100 \mu\text{A}$			1.5			V
$I_{CBO}$	$V_{CB} = 15 \text{ V}$					1.0	$\mu\text{A}$
$I_{EBO}$	$V_{EB} = 1.0 \text{ V}$					4.0	$\mu\text{A}$
$h_{FE}$	$V_{CE} = 8.0 \text{ V}$	$I_C = 200 \text{ mA}$		20		200	---
$C_{OB}$	$V_{CB} = 10 \text{ V}$	$f = 1.0 \text{ MHz}$			2.9	4.0	pF
$ S_{21} ^2$	$V_{CC} = 8.0 \text{ V}$	$I_C = 200 \text{ mA}$	$f = 1.0 \text{ GHz}$	3.5			dB
$P_{osc}$	$V_{CE} = 12 \text{ V}$	$I_C = 200 \text{ mA}$	$f = 7.5 \text{ GHz}$		630		mW